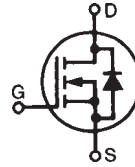


High Voltage Power MOSFET w/ Extended FBSOA

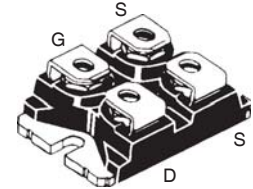
IXTN5N250

N-Channel Enhancement Mode
Avalanche Rated
Guaranteed FBSOA



$$\begin{aligned} V_{DSS} &= 2500V \\ I_{D25} &= 5A \\ R_{DS(on)} &\leq 8.8\Omega \end{aligned}$$

miniBLOC
E153432



G = Gate D = Drain
S = Source

Either Source Terminal S can be used as the Source Terminal or the Kelvin Source (Gate Return) Terminal.

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	2500	V
V_{DGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}, R_{GS} = 1M\Omega$	2500	V
V_{GSS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	$T_C = 25^\circ\text{C}$	5	A
I_{DM}	$T_C = 25^\circ\text{C}$, Pulse Width Limited by T_{JM}	20	A
I_A	$T_C = 25^\circ\text{C}$	2.5	A
E_{AS}	$T_C = 25^\circ\text{C}$	2.5	J
P_D	$T_C = 25^\circ\text{C}$	700	W
T_J		-55 to +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 to +150	$^\circ\text{C}$
V_{ISOL}	50/60 Hz, RMS, $t = 1\text{ minute}$	2500	V~
	$I_{ISOL} \leq 1\text{ mA}$, $t = 1\text{ s}$	3000	V~
M_d	Mounting Torque for Base Plate	1.5/13	Nm/lb.in.
	Terminal Connection Torque	1.3/11.5	Nm/lb.in.
Weight		30	g

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V, I_D = 1\text{ mA}$	2500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 1\text{ mA}$	2.0		5.0 V
I_{GSS}	$V_{GS} = \pm 30V, V_{DS} = 0V$			± 200 nA
I_{DSS}	$V_{DS} = 2\text{ kV}, V_{GS} = 0V$ $T_J = 125^\circ\text{C}$			50 μA 4 mA
$R_{DS(on)}$	$V_{GS} = 10V, I_D = 0.5 \cdot I_{D25}$, Note 1			8.8 Ω

Features

- International Standard Package
- Molding Epoxies Meet UL94 V-0 Flammability Classification
- Guaranteed FBSOA at 75°C
- miniBLOC with Aluminum Nitride Isolation
- Low Package Inductance

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

- High Voltage Power Supplies
- Capacitor Discharge
- Pulse Circuits

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 50\text{V}$, $I_D = 0.5 \cdot I_{D25}$, Note 1	3.0	4.5	6.0
C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$		8560	pF
C_{oss}			315	pF
C_{rss}			90	pF
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$ $R_G = 1\Omega$ (External)		33	ns
t_r			20	ns
$t_{d(off)}$			90	ns
t_f			44	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}$, $V_{DS} = 1000\text{V}$, $I_D = 0.5 \cdot I_{D25}$		200	nC
Q_{gs}			28	nC
Q_{gd}			70	nC
R_{thJC}			0.05	0.18°C/W
R_{thCS}				$^\circ\text{C/W}$

Safe Operating Area Specification

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
SOA	$V_{DS} = 2000\text{V}$, $I_D = 0.11\text{A}$, $T_C = 75^\circ\text{C}$, $t_p = 3\text{s}$	220		W

Source-Drain Diode

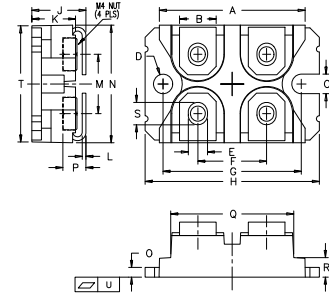
Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{V}$			5 A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			20 A
V_{SD}	$I_F = I_S$, $V_{GS} = 0\text{V}$, Note 1			1.5 V
t_{rr}	$I_F = 2.5\text{A}$, $-di/dt = 100\text{A}/\mu\text{s}$, $V_R = 100\text{V}$		1.2	μs

Note: 1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

SOT-227B (IXTN) Outline



(M4 screws (4x) supplied)

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.240	1.255	31.50	31.88
B	.307	.323	7.80	8.20
C	.161	.169	4.09	4.29
D	.161	.169	4.09	4.29
E	.161	.169	4.09	4.29
F	.587	.595	14.91	15.11
G	1.186	1.193	30.12	30.30
H	1.496	1.505	38.00	38.23
J	.460	.481	11.68	12.22
K	.351	.378	8.92	9.60
L	.030	.033	0.76	0.84
M	.496	.506	12.60	12.85
N	.990	1.001	25.15	25.42
O	.078	.084	1.98	2.13
P	.195	.235	4.95	5.97
Q	1.045	1.059	26.54	26.90
R	.155	.174	3.94	4.42
S	.186	.191	4.72	4.85
T	.968	.987	24.59	25.07
U	-.002	.004	-0.05	0.1

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

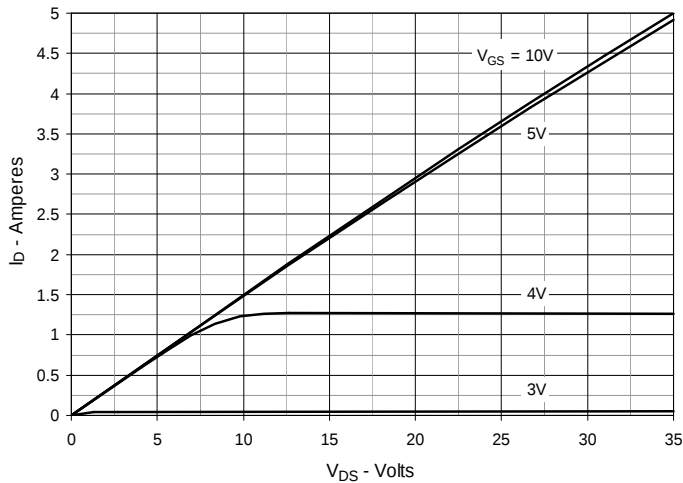
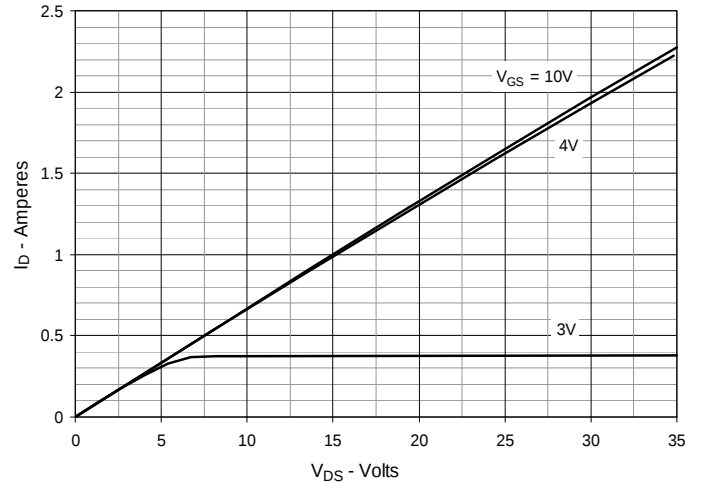
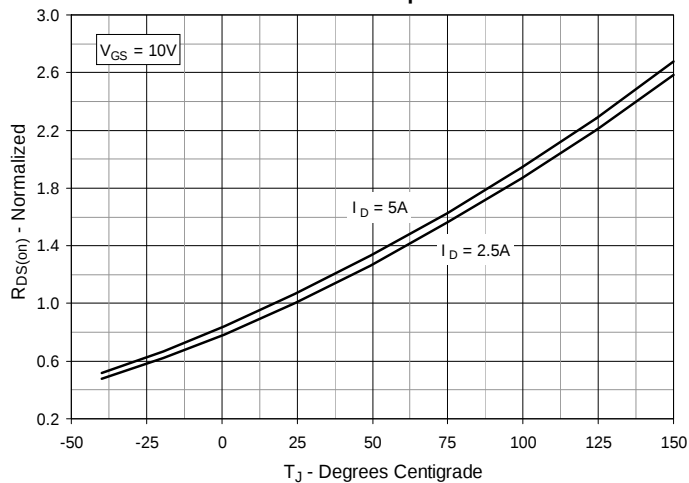
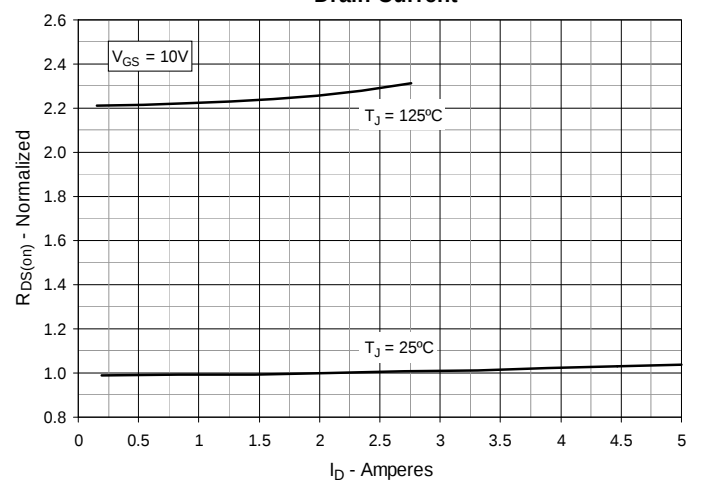
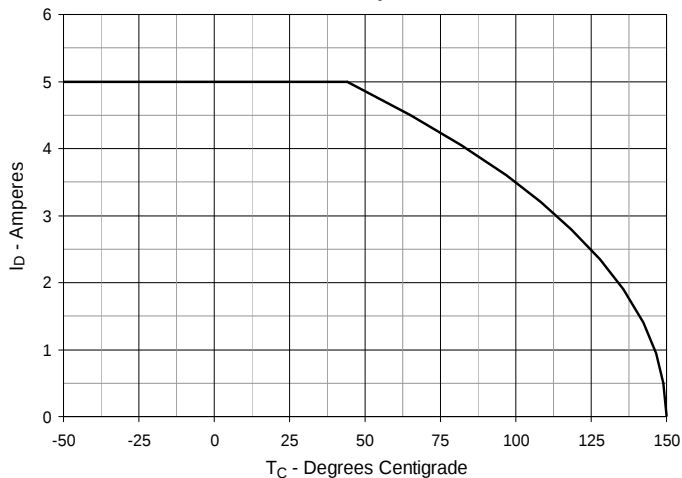
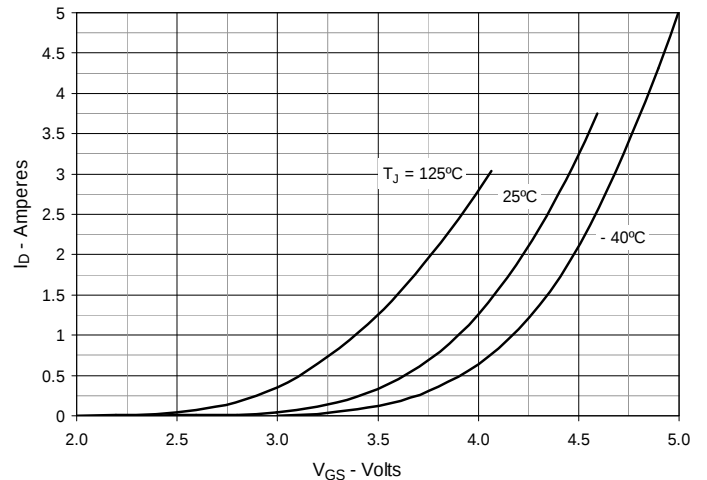
Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 2. Output Characteristics @ $T_J = 125^\circ\text{C}$

Fig. 3. $R_{DS(on)}$ Normalized to $I_D = 2.5\text{A}$ Value vs. Junction Temperature

Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 2.5\text{A}$ Value vs. Drain Current

Fig. 5. Maximum Drain Current vs. Case Temperature

Fig. 6. Input Admittance


Fig. 7. Transconductance

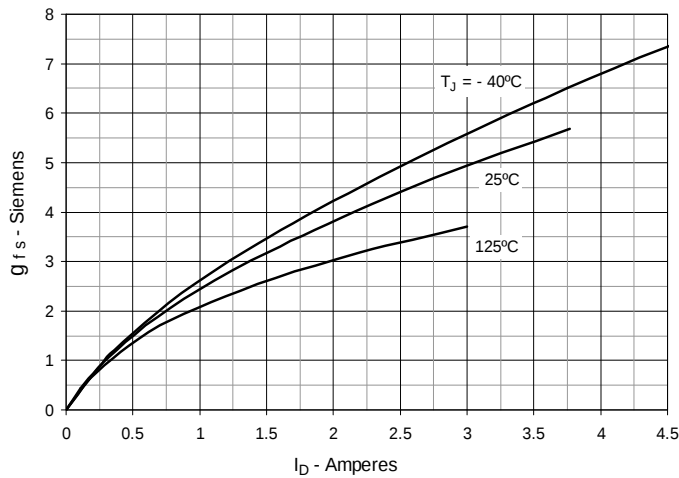


Fig. 8. Forward Voltage Drop of Intrinsic Diode

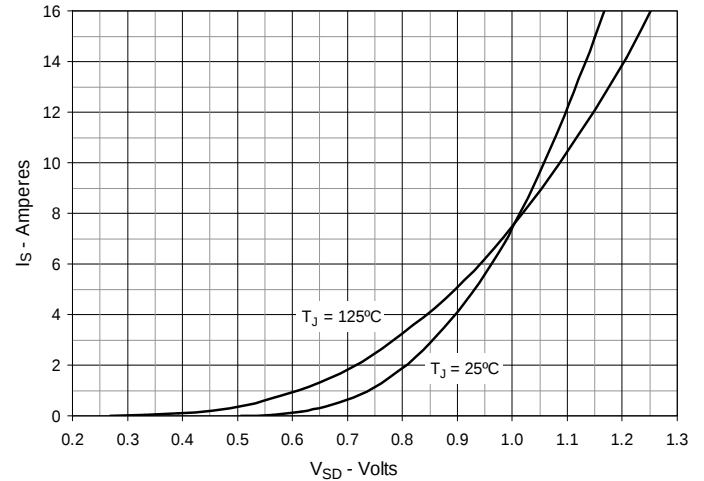


Fig. 9. Gate Charge

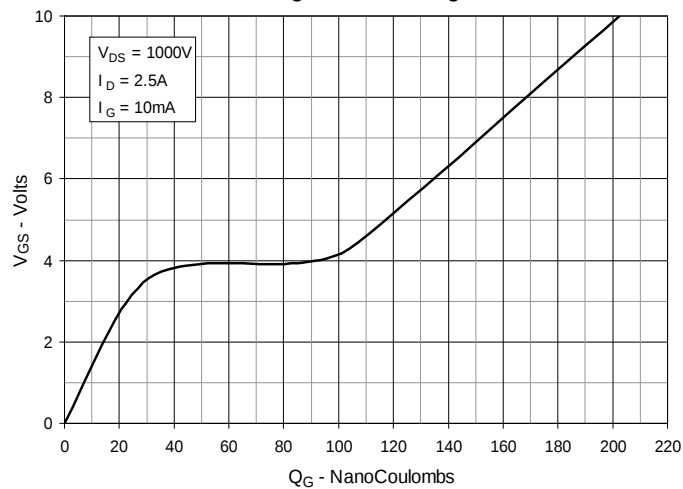


Fig. 10. Capacitance

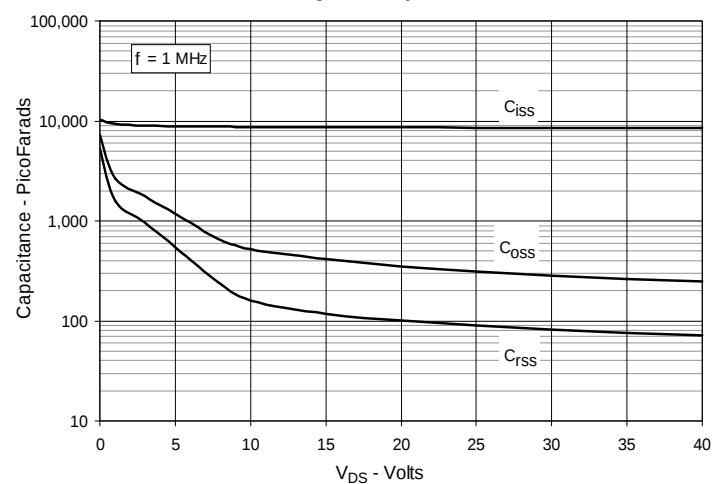


Fig. 11. Forward-Bias Safe Operating Area
@ $T_C = 25^\circ\text{C}$

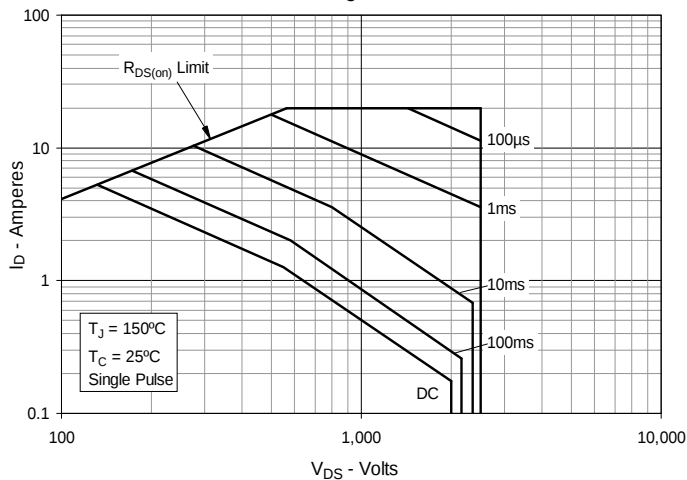


Fig. 12. Forward-Bias Safe Operating Area
@ $T_C = 75^\circ\text{C}$

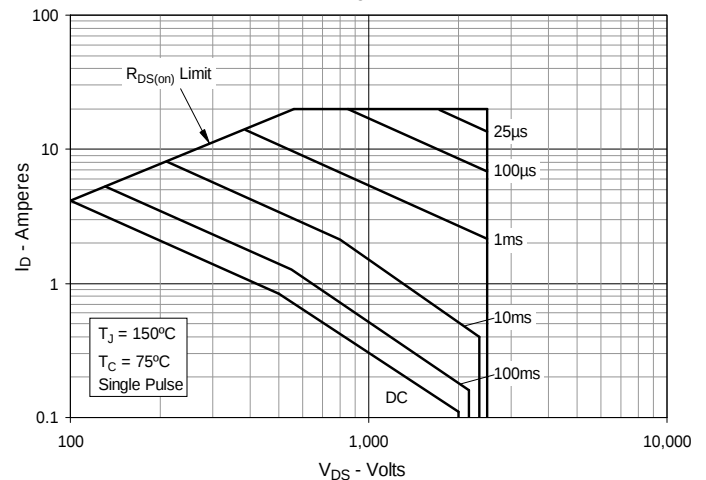


Fig. 13. Maximum Transient Thermal Impedance

